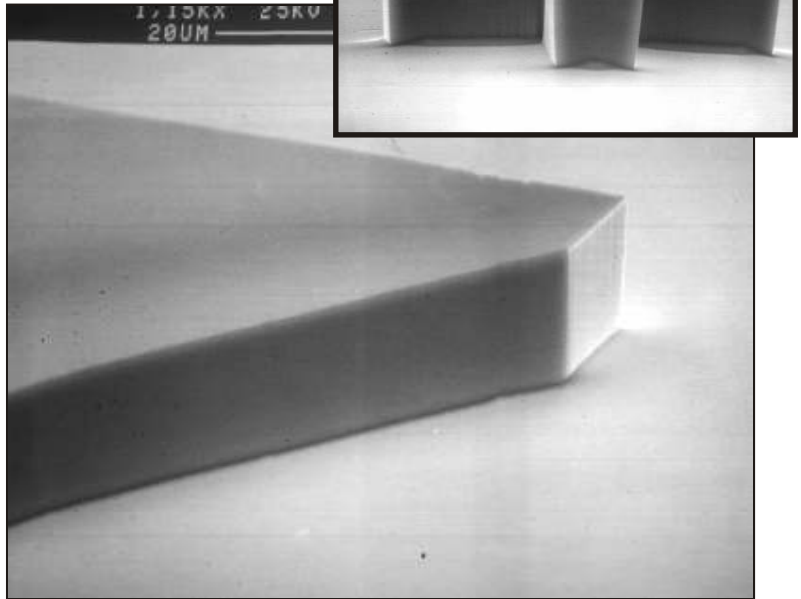
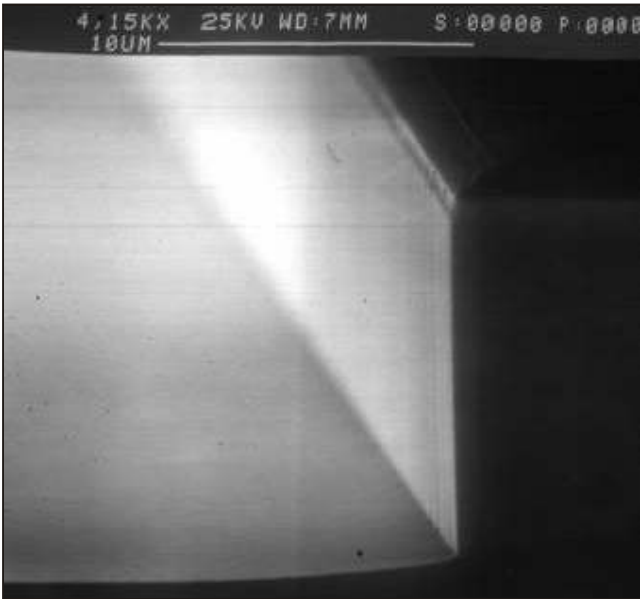
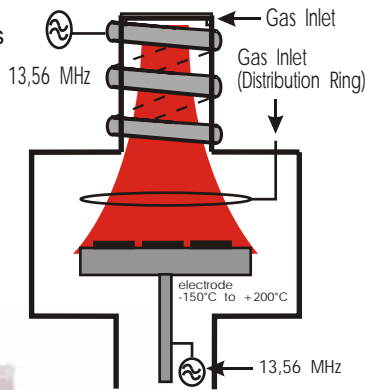


# Plasmalab Data

## Anisotropic GaAs ICP Etching



SEM's from OPT application lab in Yatton, UK, show a 18 µm deep anisotropic profile with smooth walls



**Equipment:**  
*Plasmalab System 100/ 133*

**Technology:**  
Reactive Ion Etching  
with ICP Source (13 MHz)  
Inductive Coupled Plasma  
13.56 MHz Plasma Excitation  
Chlorine based Process  
RF driven substrate electrode

**Results:**  
Rate : 1.5 µm/ min  
Selectivity to Photoresist 30 - > 100 : 1  
Selectivity to SiO<sub>2</sub> 50 - > 200 : 1  
uniformity over wafer: +/- 4 %  
low bias process for low damage

